

# 6A, 650V N-CHANNEL POWER MOSFET

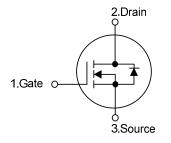
#### DESCRIPTION

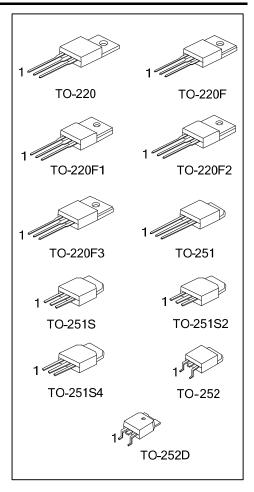
The UTC 6N65K-MT is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used in high speed switching applications of switching power supplies and adaptors.

#### FEATURES

- \*  $R_{DS(ON)}$  < 1.5 $\Omega$  @V<sub>GS</sub> = 10V,  $I_D$  = 3.0A
- \* Fast switching capability
- \* Avalanche energy tested
- \* Improved dv/dt capability, high ruggedness

### SYMBOL



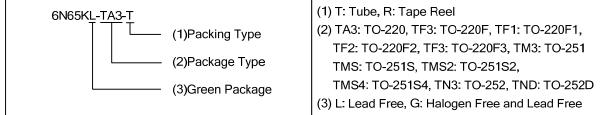


Gwww.flying1688.com www.unisonic.com.tw Copyright © 2017 Unisonic Technologies Co., Ltd

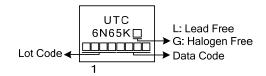
## Power MOSFET

#### ORDERING INFORMATION

Ordering Number		Dookaga	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
6N65KL-TA3-T	6N65KG-TA3-T	TO-220	G	D	S	Tube	
6N65KL-TF3-T	6N65KG-TF3-T	TO-220F	G	D	S	Tube	
6N65KL-TF1-T	6N65KG-TF1-T	TO-220F1	G	D	S	Tube	
6N65KL-TF2-T	6N65KG-TF2-T	TO-220F2	G	D	S	Tube	
6N65KL-TF3-T	6N65KG-TF3-T	TO-220F3	G	D	S	Tube	
6N65KL-TM3-T	6N65KG-TM3-T	TO-251	G	D	S	Tube	
6N65KL-TMS-T	6N65KG-TMS-T	TO-251S	G	D	S	Tube	
6N65KL-TMS2-T	6N65KG-TMS2-T	TO-251S2	G	D	S	Tube	
6N65KL-TMS4-T	6N65KG-TMS4-T	TO-251S4	G	D	S	Tube	
6N65KL-TN3-R	6N65KG-TN3-R	TO-252	G	D	S	Tape Reel	
6N65KL-TND-R	6N65KG-TND-R	TO-252D	G	D	S	Tape Reel	
Note: Pin Assignment: G: Gate D: Drain S: Source							



#### MARKING





PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V <sub>DSS</sub>	650	V
Gate-Source Voltage		V <sub>GSS</sub>	±30	V
Avalanche Current (Note 2)		I <sub>AR</sub>	6	А
Continuous Drain Current		I <sub>D</sub>	6	А
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	24	А
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	300	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	ns
Power Dissipation	TO-220		125	W
	TO-220F/TO-220F1 TO-220F3	PD	40	W
	TO-220F2		42	W
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		55	W
Junction Temperature		TJ	+150	°C
Operating Temperature		T <sub>OPR</sub>	-55 ~ +150	°C
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C

#### ABSOLUTE MAXIMUM RATINGS (T<sub>c</sub> = 25°C, unless otherwise specified)

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating : Pulse width limited by  $T_{\rm J}$
- 3. L = 16.6mH, I\_{AS} = 6A, V\_{DD} = 90V, R\_G = 25  $\Omega,$  Starting T\_J = 25°C
- 4.  $I_{SD} \le 6A$ , di/dt  $\le 200A/\mu s$ ,  $V_{DD} \le BV_{DSS}$ , Starting  $T_J = 25^{\circ}C$

#### THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT	
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-220F3	0	62.5	°C/W	
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D	θ <sub>JA</sub>	110		
Junction to Case	TO-220		1.0		
	TO-220F/TO-220F1 TO-220F3		3.2		
	TO-220F2	θ <sub>JC</sub>	2.97	°C/W	
	TO-251/TO-251S TO-251S2/TO-251S4 TO-252/TO-252D		2.27		

UNISONIC TECHINOLOGIES CO., LTD

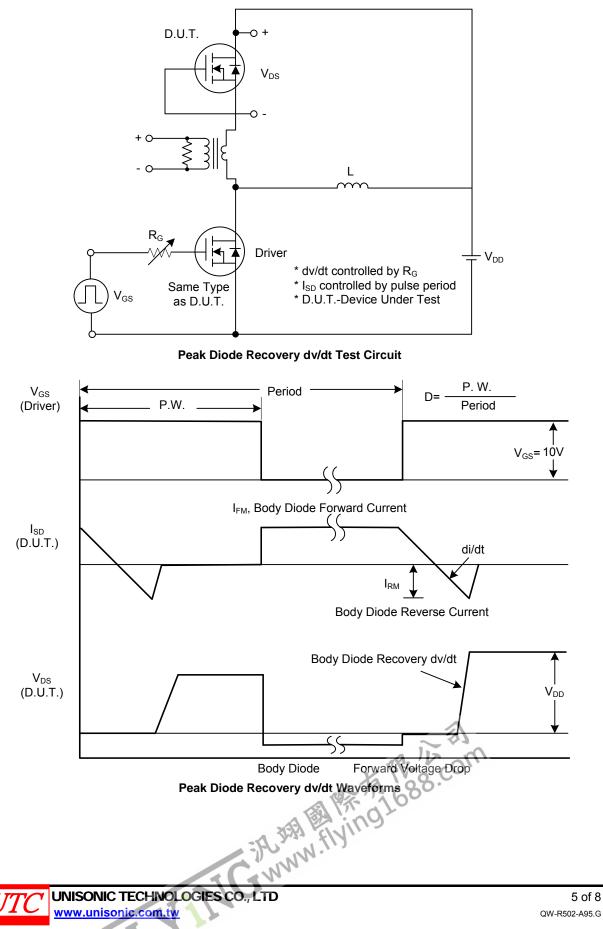
				N ALNI			
		SYMBOL	TEST CONDITIONS	IVIIIN	ΙΥΡ	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	$V_{GS} = 0V, I_D = 250\mu A$	650			V
Drain-Source Leakage Current		I <sub>DSS</sub>	$V_{DS} = 650V, V_{GS} = 0V$			10	μA
Gate- Source Leakage Current	Forward	- I <sub>GSS</sub>	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse		$V_{GS}$ = -30V, $V_{DS}$ = 0V			-100	nA
Breakdown Voltage Temperature Coefficient		$\bigtriangleup BV_{\text{DSS}} / \bigtriangleup T_J$	I <sub>D</sub> =250µA, Referenced to 25°C		0.53		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V <sub>GS(TH)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$			4.0	V
Static Drain-Source On-State Resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.0A			1.5	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C <sub>ISS</sub>			875	1000	pF
Output Capacitance		C <sub>OSS</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0 MHz		88	120	рF
Reverse Transfer Capacitance		C <sub>RSS</sub>			8	25	pF
SWITCHING CHARACTERISTIC	s						
Turn-On Delay Time		t <sub>D(ON)</sub>			40	48	ns
Turn-On Rise Time		t <sub>R</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =0.5A,		44	53	ns
Turn-Off Delay Time		t <sub>D(OFF)</sub>	R <sub>G</sub> =25Ω (Note 1, 2)		190	230	ns
Turn-Off Fall Time		t <sub>F</sub>			40	50	ns
Total Gate Charge		Q <sub>G</sub>			67	80	nC
Gate-Source Charge Gate-Drain Charge		Q <sub>GS</sub>	$V_{DS}$ =50V, I <sub>D</sub> =1.3A,		6.8		nC
		$Q_{GD}$	V <sub>GS</sub> =10V (Note 1, 2)		6.2		nC
DRAIN-SOURCE DIODE CHARA	CTERISTIC		MUM RATINGS				
Drain-Source Diode Forward Volta	age	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 6 A			1.4	V
Maximum Continuous Drain-Sourc	ce Diode					<u> </u>	•
Forward Current		I <sub>S</sub>				6	A
Maximum Pulsed Drain-Source Diode		I <sub>SM</sub>				24	А
Forward Current						24	А

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

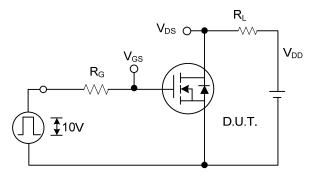
Notes: 1. Pulse Test: Pulse width  $\leq$  300µs, Duty cycle  $\leq$  2%

2. Essentially independent of operating temperature

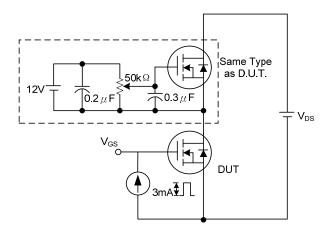
### TEST CIRCUITS AND WAVEFORMS



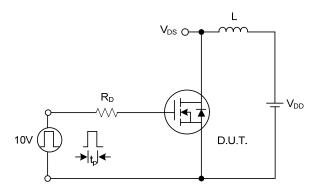
### ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



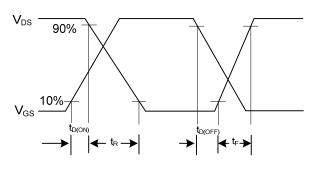
### Switching Test Circuit



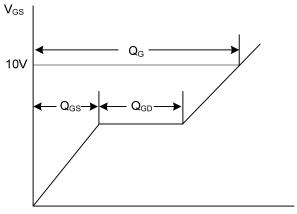
#### **Gate Charge Test Circuit**



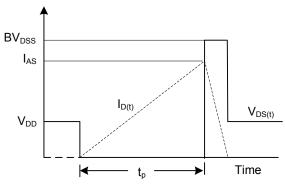
**Unclamped Inductive Switching Test Circuit** 



Switching Waveforms



Charge Gate Charge Waveform

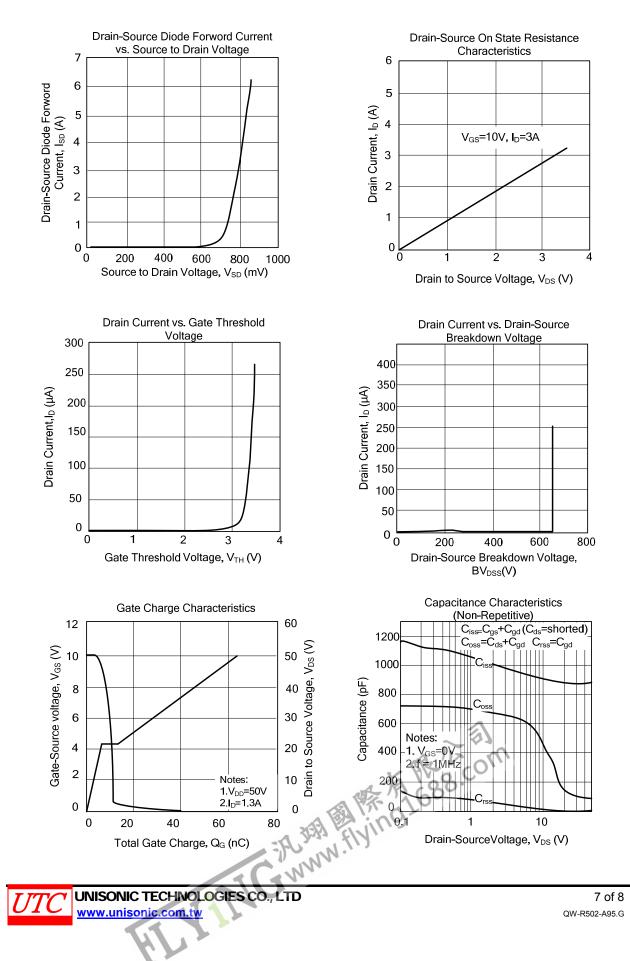


**Unclamped Inductive Switching Waveforms** 

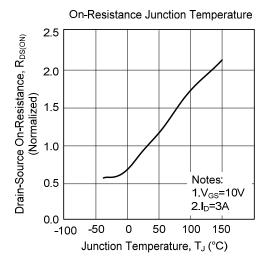


### **Power MOSFET**

### TYPICAL CHARACTERISTICS



### ■ TYPICAL CHARACTERISTICS (Cont.)



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

